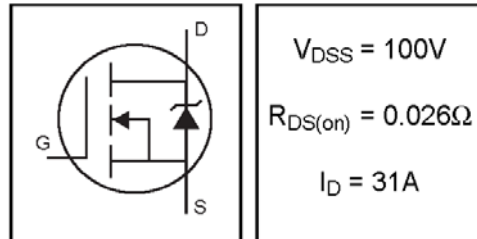


# IRLI2910PbF

HEXFET® Power MOSFET

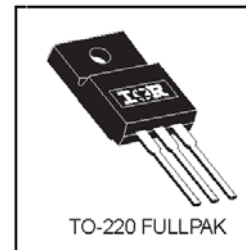
- Logic-Level Gate Drive
- Advanced Process Technology
- Ultra Low On-Resistance
- Isolated Package
- High Voltage Isolation = 2.5KV RMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free



### Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.



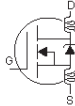
### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	31	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	22	
$I_{DM}$	Pulsed Drain Current ①⑥	190	
$P_D @ T_C = 25^\circ C$	Power Dissipation	63	W
	Linear Derating Factor	0.42	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 16$	V
$E_{AS}$	Single Pulse Avalanche Energy ②⑥	520	mJ
$I_{AR}$	Avalanche Current ①⑥	29	A
$E_{AR}$	Repetitive Avalanche Energy ①	6.3	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ ③⑥	5.0	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf·in (1.1 N·m)	

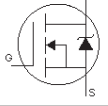
### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	65	°C/W

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.12	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA <sup>⑥</sup>
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.026	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 16A <sup>④</sup>
		—	—	0.030		V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 16A <sup>④</sup>
		—	—	0.040		V <sub>GS</sub> = 4.0V, I <sub>D</sub> = 14A <sup>④</sup>
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	28	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 29A <sup>⑥</sup>
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -16V
Q <sub>g</sub>	Total Gate Charge	—	—	140	nC	I <sub>D</sub> = 29A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	20		V <sub>DS</sub> = 80V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	81		V <sub>GS</sub> = 5.0V, See Fig. 6 and 13 <sup>④⑤</sup>
t <sub>d(on)</sub>	Turn-On Delay Time	—	11	—	ns	V <sub>DD</sub> = 50V
t <sub>r</sub>	Rise Time	—	100	—		I <sub>D</sub> = 29A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	49	—		R <sub>G</sub> = 1.4Ω, V <sub>GS</sub> = 5.0V
t <sub>f</sub>	Fall Time	—	55	—		R <sub>D</sub> = 1.7Ω, See Fig. 10 <sup>④⑤</sup>
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	3700	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	630	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	330	—		f = 1.0MHz, See Fig. 5 <sup>⑥</sup>
C	Drain to Sink Capacitance	—	12	—		f = 1.0MHz

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	31	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) <sup>①⑥</sup>	—	—	190		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 16A, V <sub>GS</sub> = 0V <sup>④</sup>
t <sub>rr</sub>	Reverse Recovery Time	—	240	350	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 29A
Q <sub>rr</sub>	Reverse Recovery Charge	—	1.8	2.7	μC	di/dt = 100A/μs <sup>④⑤</sup>

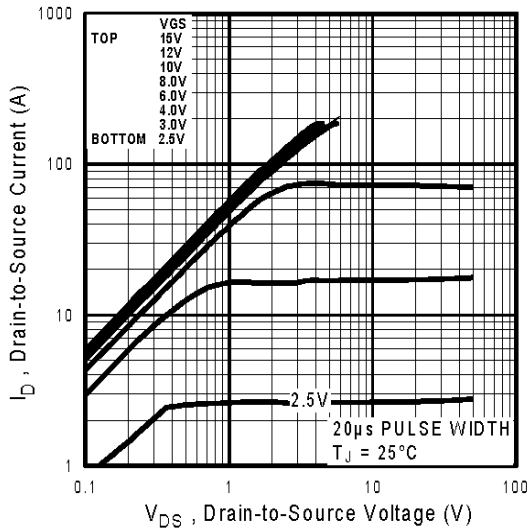
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② V<sub>DD</sub> = 25V, starting T<sub>J</sub> = 25°C, L = 1.2mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 29A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ 29A, di/dt ≤ 490A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 175°C

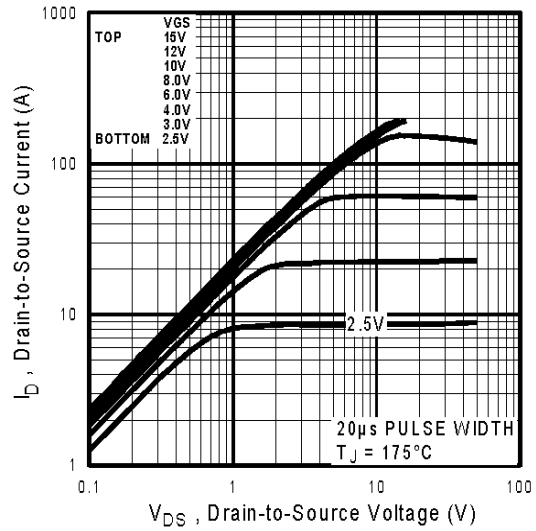
④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ t = 60s, f = 60Hz

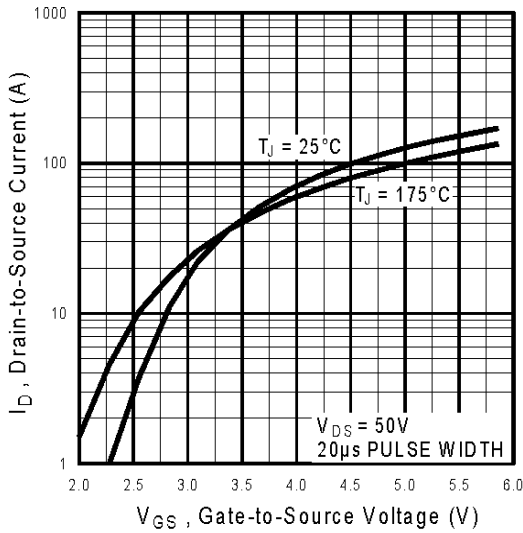
⑥ Uses IRL2910 data and test conditions



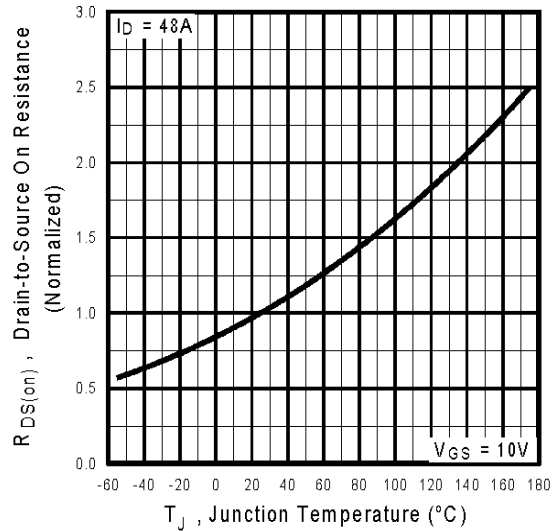
**Fig 1.** Typical Output Characteristics



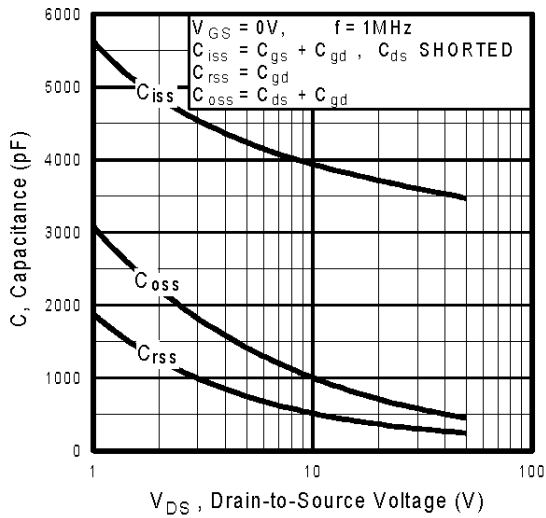
**Fig 2.** Typical Output Characteristics



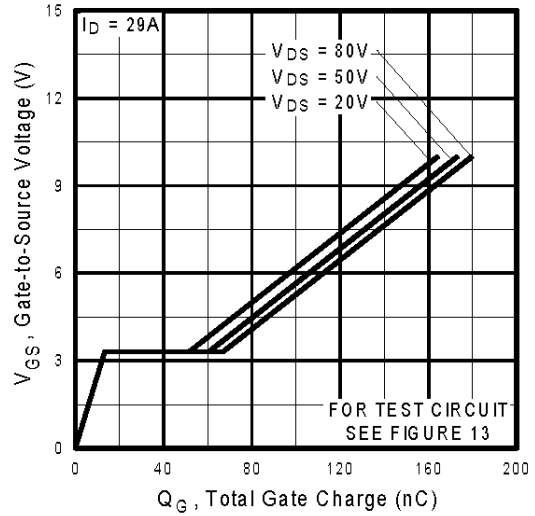
**Fig 3.** Typical Transfer Characteristics



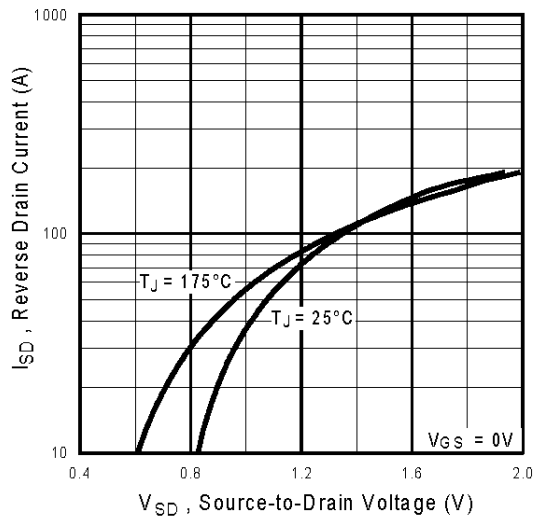
**Fig 4.** Normalized On-Resistance Vs. Temperature



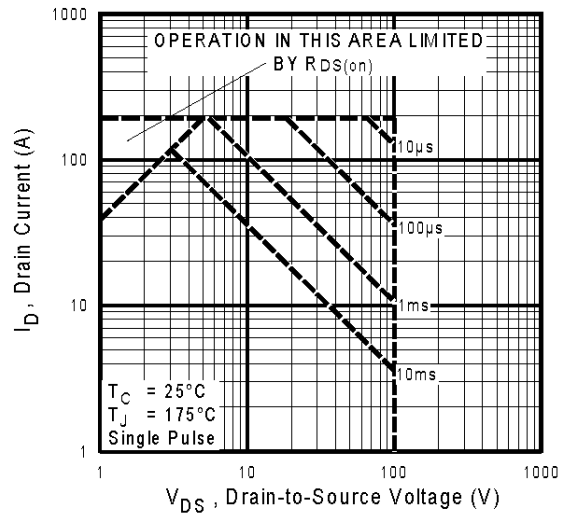
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



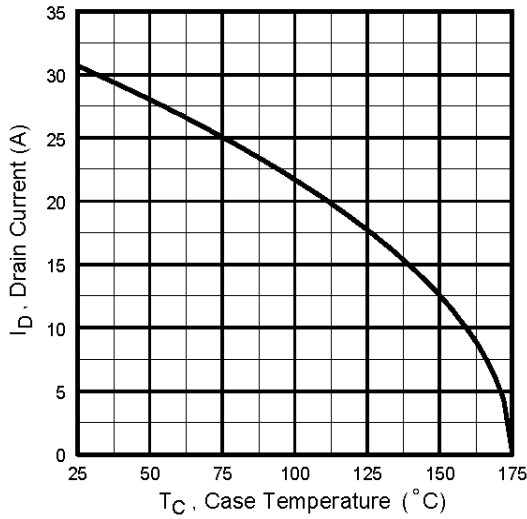
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



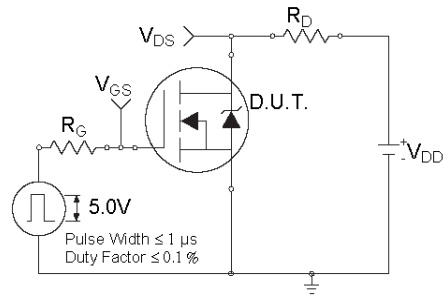
**Fig 7.** Typical Source-Drain Diode Forward Voltage



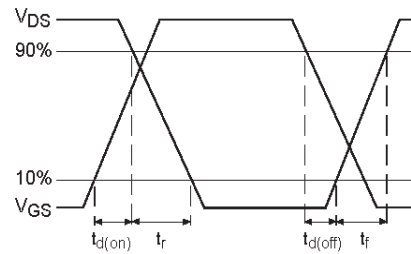
**Fig 8.** Maximum Safe Operating Area



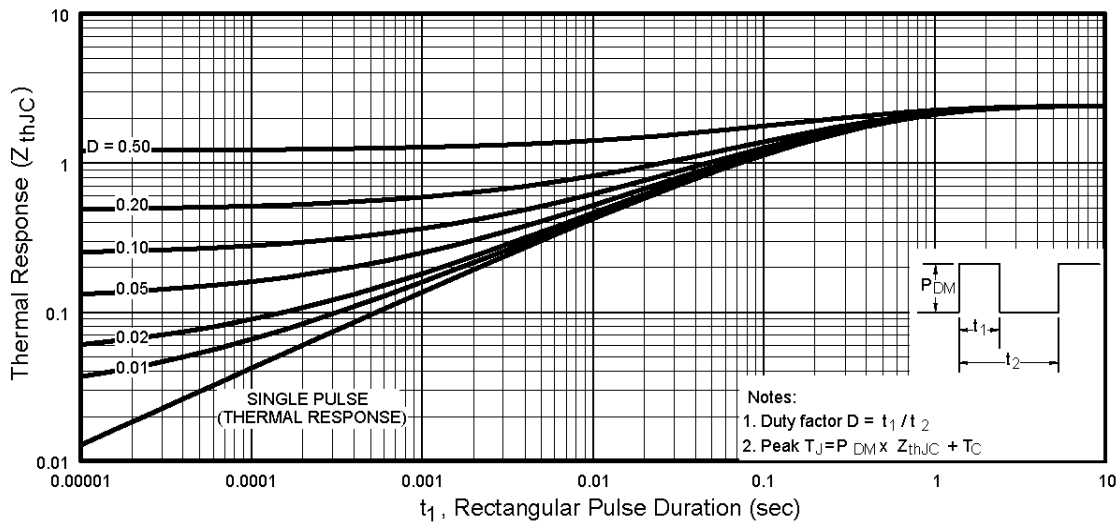
**Fig 9.** Maximum Drain Current Vs. Case Temperature



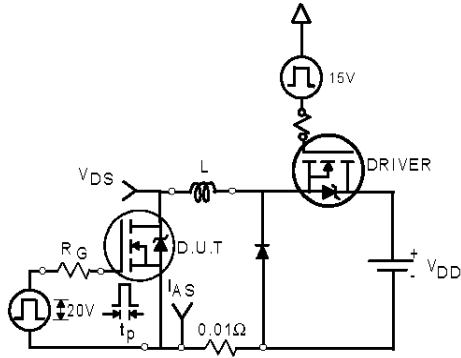
**Fig 10a.** Switching Time Test Circuit



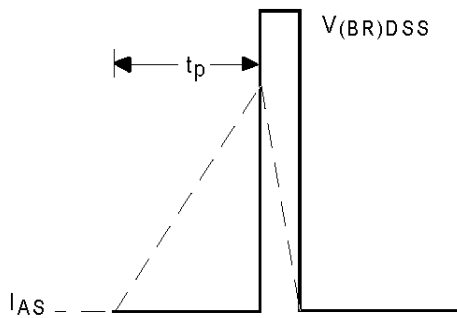
**Fig 10b.** Switching Time Waveforms



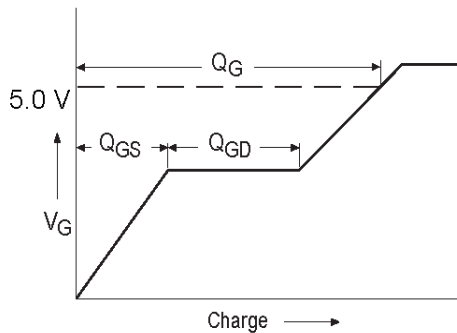
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



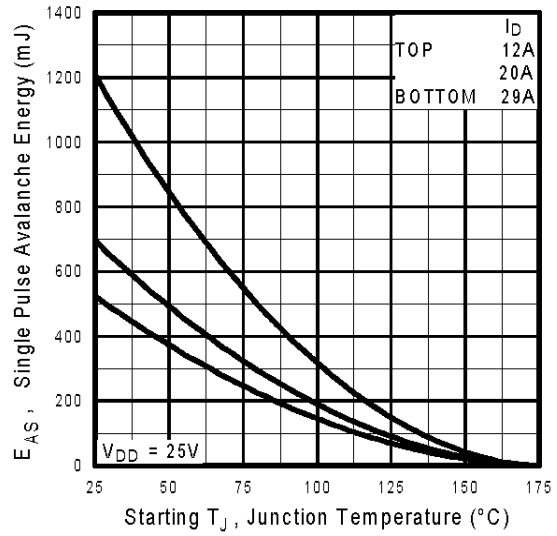
**Fig 12a.** Unclamped Inductive Test Circuit



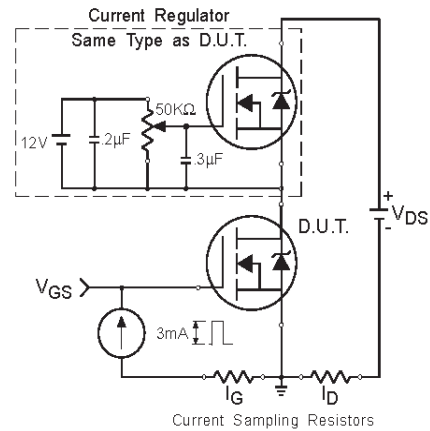
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

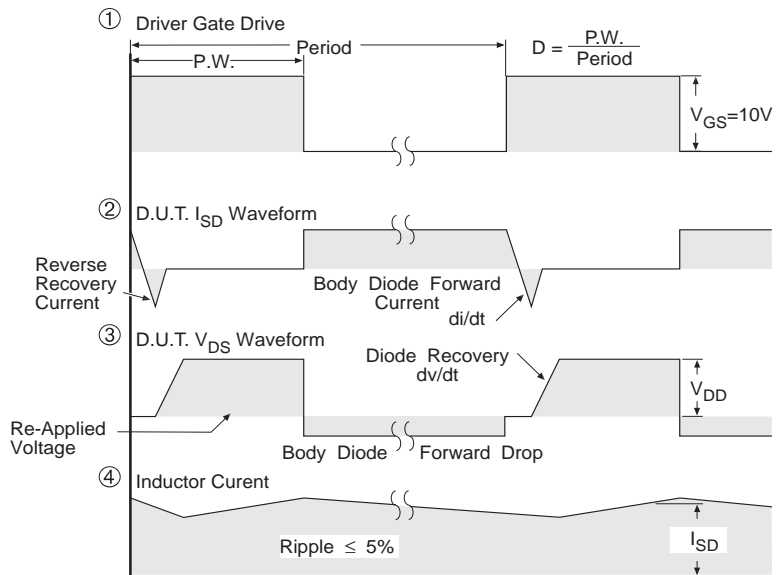


**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\* Reverse Polarity for P-Channel  
\*\* Use P-Channel Driver for P-Channel Measurements



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

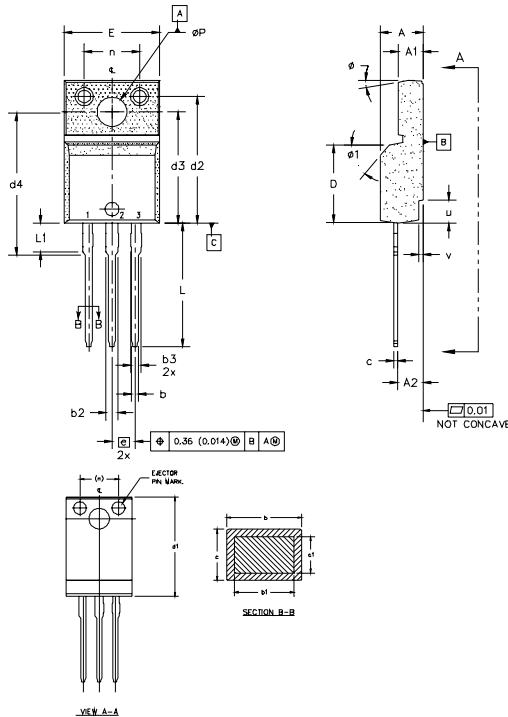
**Fig -14 For N Channel HEXFETS**

# IRLI2910PbF

International  
**IR** Rectifier

## TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



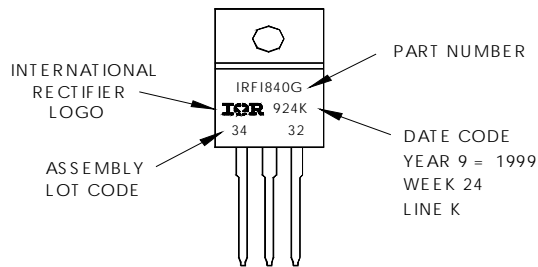
- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  - 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 5.0 DIMENSION D1 APPLY TO BASE METAL ONLY.
  - 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
  - 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES	LEAD ASSIGNMENTS
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.57	4.83	0.180	0.190		
A1	2.57	2.83	0.101	0.114		
A2	2.51	2.85	0.099	0.112		
b	0.622	0.89	0.024	0.035		HEXFET
b1	0.622	0.838	0.024	0.033	5	1.- GATE 2.- DRAIN 3.- SOURCE
b2	1.229	1.400	0.048	0.055		
b3	1.229	1.400	0.048	0.055		
c	0.440	0.629	0.017	0.025		
c1	0.440	0.564	0.017	0.023	4	IRBta CoPACK
D	8.65	9.80	0.341	0.396		1.- GATE 2.- COLLECTOR 3.- EMITTER
d1	15.80	16.12	0.622	0.635		
d2	13.97	14.22	0.550	0.560		
d3	12.30	12.92	0.484	0.509		
d4	8.64	9.91	0.340	0.390		
E	10.36	10.63	0.408	0.419	4	
e	2.54 BSC		0.100 BSC			
L	13.20	13.73	0.520	0.541		
L1	3.10	3.50	0.122	0.138	3	
n	6.05	6.15	0.238	0.242		
φP	3.05	3.45	0.120	0.136		
u	2.40	2.50	0.094	0.098	6	
v	0.40	0.50	0.016	0.020	6	
φ1	3°	7°	3°	7°		
φ1		45°		45°		

## TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G  
WITH ASSEMBLY  
LOT CODE 3432  
ASSEMBLED ON WW 24 1999  
IN THE ASSEMBLY LINE "K"

**Note:** "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

International  
**IR** Rectifier

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TAC Fax: (310) 252-7903

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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>